# N-Channel Depletion-Mode Vertical DMOS FET

## Features

- High input impedance
- Low input capacitance
- Fast switching speeds
- Low on-resistance
- Free from secondary breakdown
- Low input and output leakage

## Applications

- Normally-on switches
- Solid state relays
- Converters
- Linear amplifiers
- Constant current sources
- Telecom

## General Description

This depletion-mode (normally-on) transistor utilizes an advanced vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

## Ordering Information

| Device | Package Option | $BV_{DSX}/BV_{DGX}$ (V) | $R_{DS(ON)}$ (max) (Ω) | $I_{DSS}$ (min) (mA) |
|---|---|---|---|---|
| | TO-252 (D-PAK) | | | |
| DN3765 | DN3765K4-G | 650 | 8.0 | 200 |

*-G indicates package is RoHS compliant ('Green')*

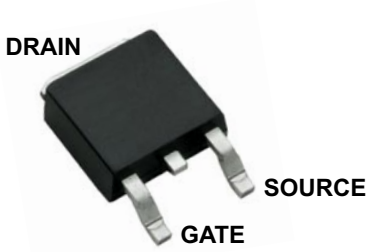
## Absolute Maximum Ratings

| Parameter | Value |
|---|---|
| Drain-to-source voltage | $BV_{DSX}$ |
| Drain-to-gate voltage | $BV_{DGX}$ |
| Gate-to-source voltage | ±20V |
| Operating and storage temperature | -55°C to +150°C |
| Maximum junction temperature* | 150°C |

*Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.*

** Distance of 1.6mm from case for 10 seconds.*

## Pin Configuration




**TO-252 (D-PAK) (K4)**

## Product Marking


YY = Year Sealed
WW = Week Sealed
L = Lot Number
_____= "Green" Packaging

**TO-252 (D-PAK) (K4)**

## Thermal Characteristics

| Package | $I_D$ (continuous)† (A) | $I_D$ (pulsed) (A) | Power Dissipation ‡ @$T_A$ = 25°C (W) | $\theta_{jc}$ (°C/W) | $\theta_{ja}$ (°C/W) | $I_{DR}$ † (A) | $I_{DRM}$ (A) |
|---|---|---|---|---|---|---|---|
| TO-252 (D-PAK) | 0.30 | 0.50 | 2.5 | 6.25 | 50 | 0.30 | 0.50 |

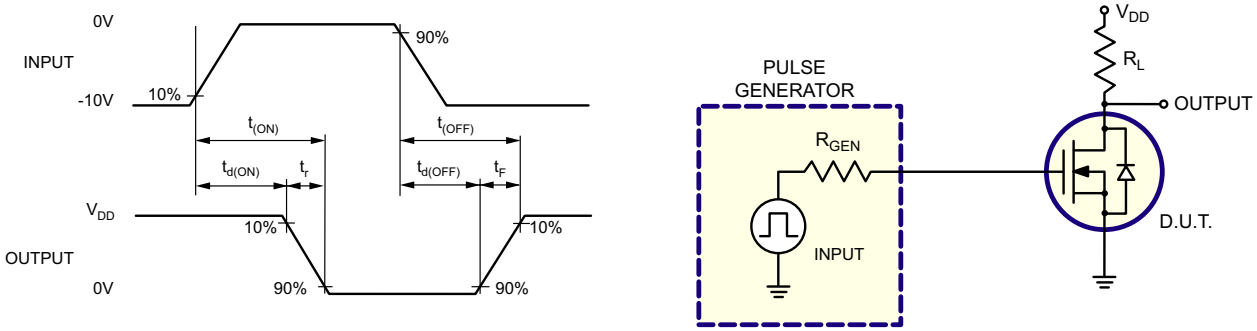
***Notes:***
† $I_D$ (continuous) is limited by max rated $T_j$ of 150°C.
‡ Mounted on FR4 board, 25mm x 25mm x 1.57mm.

## Electrical Characteristics ($T_A$ = 25°C unless otherwise specified)

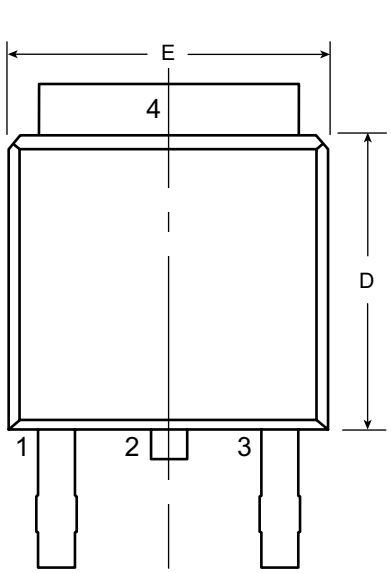
| Sym | Parameter | Min | Typ | Max | Units | Conditions |
|---|---|---|---|---|---|---|
| $BV_{DSX}$ | Drain-to-source breakdown voltage | 650 | - | - | V | $V_{GS}$ = -5.0V, $I_D$ = 100µA |
| $V_{GS(OFF)}$ | Gate-to-source off voltage | -1.5 | - | -3.5 | V | $V_{DS}$ = 25V, $I_D$= 10µA |
| $\Delta V_{GS(OFF)}$ | Change in $V_{GS(OFF)}$ with temperature | - | - | -4.5 | mV/°C | $V_{DS}$ = 25V, $I_D$= 10µA |
| $I_{GSS}$ | Gate body leakage current | - | - | 100 | nA | $V_{GS}$ = ± 20V, $V_{DS}$ = 0V |
| $I_{D(OFF)}$ | Drain-to-source leakage current | - | - | 10 | µA | $V_{GS}$ = -10V, $V_{DS}$ = Max Rating |
| | | - | - | 1.0 | mA | $V_{GS}$ = -10V, $V_{DS}$ = 0.8 Max Rating, $T_A$ = 125°C |
| $I_{DSS}$ | Saturated drain-to-source current | 200 | - | - | mA | $V_{GS}$ = 0V, $V_{DS}$ = 25V |
| $R_{DS(ON)}$ | Static drain-to-source on-state resistance | - | - | 8.0 | Ω | $V_{GS}$ = 0V, $I_D$ = 150mA |
| $\Delta R_{DS(ON)}$ | Change in $R_{DS(ON)}$ with temperature | - | - | 1.1 | %/°C | $V_{GS}$ = 0V, $I_D$ = 150mA |
| $G_{FS}$ | Forward transductance | 100 | - | - | mmho | $I_D$ = 100mA, $V_{DS}$ = 10V |
| $C_{ISS}$ | Input capacitance | - | - | 825 | pF | $V_{GS}$ = -10V, $V_{DS}$ = 25V, f = 1.0MHz |
| $C_{OSS}$ | Common source output capacitance | - | - | 190 | | |
| $C_{RSS}$ | Reverse transfer capacitance | - | - | 110 | | |
| $t_{d(ON)}$ | Turn-on delay time | - | - | 50 | ns | $V_{DD}$ = 25V, $I_D$ = 150mA, $R_{GEN}$ = 25Ω |
| $t_r$ | Rise time | - | - | 75 | | |
| $t_{d(OFF)}$ | Turn-off delay time | - | - | 75 | | |
| $t_f$ | Fall time | - | - | 100 | | |
| $V_{SD}$ | Diode forward voltage drop | - | - | 1.8 | V | $V_{GS}$ = -5.0V, $I_{SD}$ = 200mA |
| $t_{rr}$ | Reverse recovery time | - | 800 | - | ns | $V_{GS}$ = -5.0V, $I_{SD}$ = 200mA |

***Notes:***
1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.

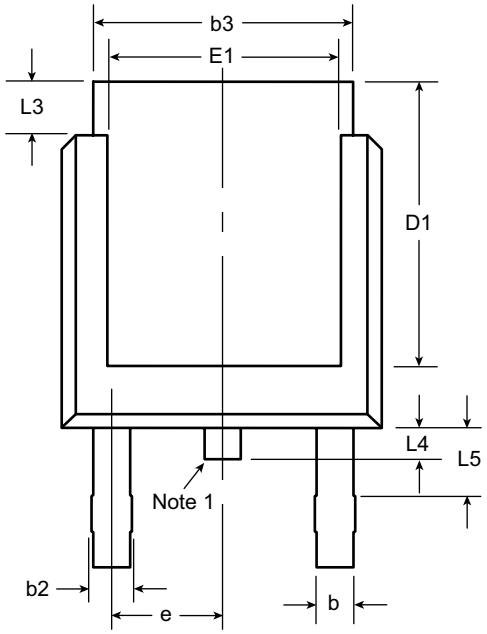
## Switching Waveforms and Test Circuit



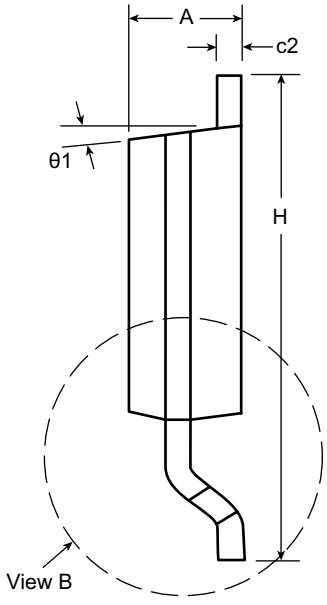
# 3-Lead TO-252 D-PAK Package Outline (K4)



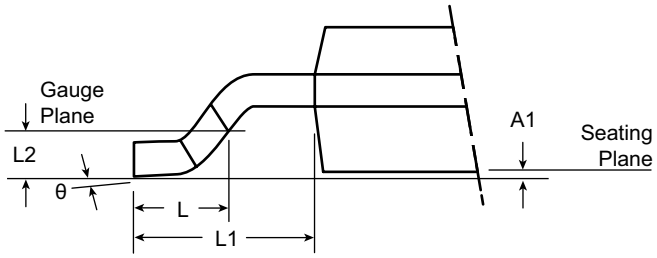

**Front View**




**Rear View**




**Side View**




**View B**

***Note:***

1. *Although 4 terminal locations are shown, only 3 are functional. Lead number 2 was removed.*

| Symbol | | A | A1 | b | b2 | b3 | c2 | D | D1 | E | E1 | e | H | L | L1 | L2 | L3 | L4 | L5 | θ | θ1 |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| Dimen-sion (inches) | MIN | .086 | .000* | .025 | .030 | .195 | .018 | .235 | .205 | .250 | .170 | .090 BSC | .370 | .055 | .108 REF | .020 BSC | .035 | .025* | .045 | $0^0$ | $0^0$ |
| | NOM | - | - | - | - | - | - | .240 | - | - | - | | - | .060 | | | - | - | - | - | - |
| | MAX | .094 | .005 | .035 | .045 | .215 | .035 | .245 | .217* | .265 | .182* | | .410 | .070 | | | .050 | .040 | .060 | $10^0$ | $15^0$ |

*JEDEC Registration TO-252, Variation AA, Issue E, June 2004.*
** This dimension is not specified in the original JEDEC drawing. The value listed is for reference only.*
***Drawings not to scale.***
***Supertex Doc. #:*** *DSPD-3TO252K4, Version D081408.*

*(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)*



Supertex inc.
1235 Bordeaux Drive, Sunnyvale, CA 94089
Tel: 408-222-8888
www.supertex.com